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(54) Title: LOW CAPACITANCE LOW RC WRAP-AROUND-CONTACT

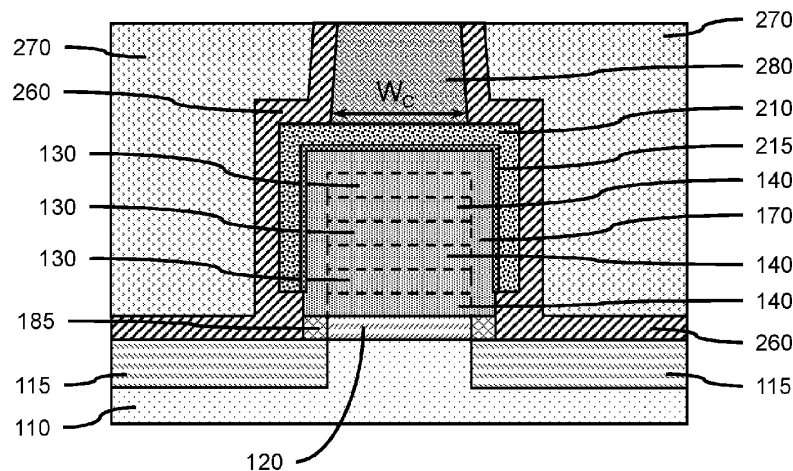


FIG. 20

(57) Abstract: A field effect transistor is provided. The field effect transistor includes a first source/drain (170) on a substrate (110), a second source/drain on the substrate, and a channel region (130) between the first source/drain and the second source/drain. The field effect transistor further includes a metal liner (210) on at least three sides of the first source/drain and/or the second source/drain, wherein the metal liner covers less than the full height of a sidewall of the first source/drain and/or the second source/drain. The field effect transistor further includes a metal-silicide (215) between the metal liner and the first source/drain and/or the second source/drain, and a conductive contact (218) on the metal liner on the first source/drain and/or the second source/drain, wherein the conductive contact is a conductive material different from the conductive material of the metal liner. An amorphization step is performed after forming the source/drain and before depositing the metal liner.

[Continued on next page]

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